

# AlSiC Microprocessor Applications

## Thermal Management

- Controlled thermal expansion compatible with die or substrates
- High thermal conductivity with controlled CTE improves thermal dissipation

## Net Shape Casting Technology

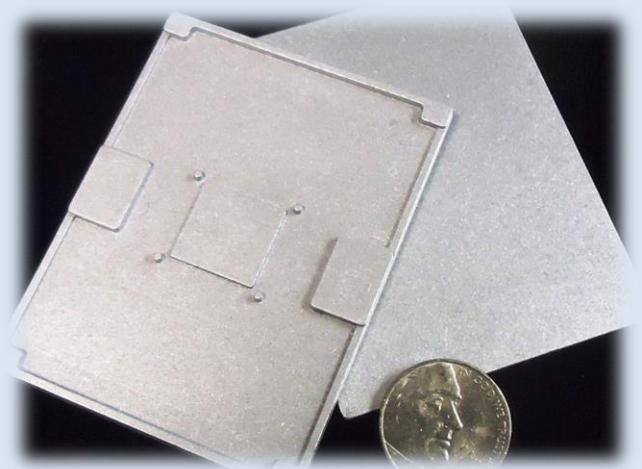
- Tight dimensional control of cavity depth
- Complex shapes without machining
- Cost effective, high volume manufacturing

## Lightweight Material

- Large formats (>50 mm square) possible with little weight penalty
- Reduces weight per solder ball in BGAs

## High Strength, High Stiffness

- Reduces assembly warping
- Thinner bond line with reproducible thickness

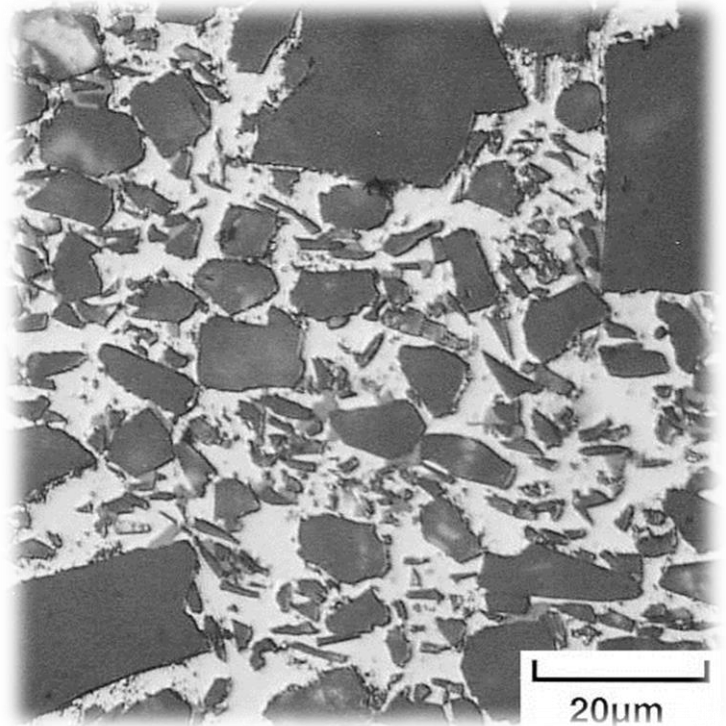


## AISiC Material Properties

**CPS AISiC** combines aluminum metal and silicon carbide particulates to obtain material properties ideally suited for Flip Chip and Microprocessor Lids that require good thermal conductivity and a compatible thermal expansion for thermal management.

Thermal management also requires shape and stiffness to maintain a thin TIM1 bond line during product life. A stiff lid will control warping and bowing during assembly to improve solder attachment; it also reduces warping during cycling to maintain a thin TIM1 bond line for the best thermal dissipation and device performance.

AISiC is a lightweight lid material that reduces weight per solder ball and will make a package insensitive to orientation dependence. Large format lids can be considered with AISiC which enable integrated SIP designs.



	<b>AISiC-9</b>	<b>AISiC-12</b>
Aluminum Alloy 356	37 vol%	63 vol%
Silicon Carbide (electronic grade)	63 vol%	37 vol%
Density (g/cm <sup>3</sup> )	3.01	2.89
Thermal Conductivity (W/mK) @25°C	190 typical (180 W/mK min)	180 typical (170 W/mK min)
Specific Heat (J/gK) @ 25°C	0.741	0.808
Thermal Expansion (CTE) ppm/°C		
30 – 100°C	8.00 $\sigma = 0.26$	10.9 $\sigma = 0.25$
30 – 150°C	8.37 $\sigma = 0.26$	11.2 $\sigma = 0.25$
30 – 200°C	8.75 $\sigma = 0.27$	11.7 $\sigma = 0.25$
Young's Modulus (GPa)	188	167
Shear Modulus (GPa)	76	69
Strength (MPa) a-bar 4pt-bend	488	471
Percent Elongation at Rupture	0.295	N/A
Fracture Toughness	11.3	N/A
Electrical Resistance ( $\mu$ Ohm-cm)	20.7	20.7
Hermeticity (atm-cm <sup>3</sup> /s He)	< 10 <sup>-9</sup>	< 10 <sup>-9</sup>

CPS Technologies Corporation  
 111 South Worcester Street, Norton, MA 02766  
 508 222-0614

[www.alsic.com](http://www.alsic.com)

# AISiC with High Thermal Dissipation Pyrolytic Graphite

## AISiC Pyrolytic Graphite Composite

- **CTE** – 50% of Cu at 8.5 ppm/°C
- **TC** – 200% of Cu at 1000 W/mK<sup>1</sup>
- **Density** – 33% of Cu at 3.0 g/cm<sup>3</sup>

## AISiC

- Low thermal expansion compatible with electronics and dielectric substrates
- Lightweight, high strength and stiffness composite
- Functional net shape cast design
- Provides a hermetic, strong envelope material for low strength, environmentally sensitive pyrolytic graphite

## Pyrolytic Graphite

- Lightweight material that provides high heat spreading, 1300 W/mK in X,Y plane; 30 W/mK in Z direction

## AISiC/Pyrolytic Composite

- Has an effective thermal conductivity of 1000 W/mK<sup>1</sup>

## Applications

- Radar systems
- Airborne & Space electronics
- Edge-cooled / Conduction-cooled electronics
- Lightweight passive cooling mobile applications

<sup>1</sup> heat dissipation will be a function of design and thermal path

